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Kind regards,

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BUK761R7-40E

N-channel TrenchMOS standard level FET

19 May 2016 **Product data sheet**

1. General description

Standard level N-channel MOSFET in a SOT404A package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with $V_{GS(th)}$ rating of greater than 1 V at 175 °C

3. Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

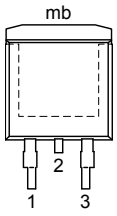
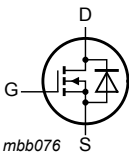
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	-	40	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 2	[1]	-	-	120	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	-	324	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		-	1.32	1.6	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; Fig. 13; Fig. 14		-	34.7	-	nC

[1] Continuous current is limited by package.

Scan or click this QR code to view the latest information for this product

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 D2PAK (SOT404A)	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK761R7-40E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404A

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK761R7-40E	BUK761R7-40E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	40	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ		-	40	V
V_{GS}	gate-source voltage	DC; T_j ≤ 175 °C		-20	20	V
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	324	W
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 2	[1]	-	120	A
		V_{GS} = 10 V; T_{mb} = 100 °C; Fig. 2		-	120	A
I_{DM}	peak drain current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C; Fig. 3		-	1306	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[1]	-	120	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C		-	1306	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 120 A; $V_{sup} \leq 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[2][3]	-	801	mJ

[1] Continuous current is limited by package.
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
[3] Refer to application note AN10273 for further information.

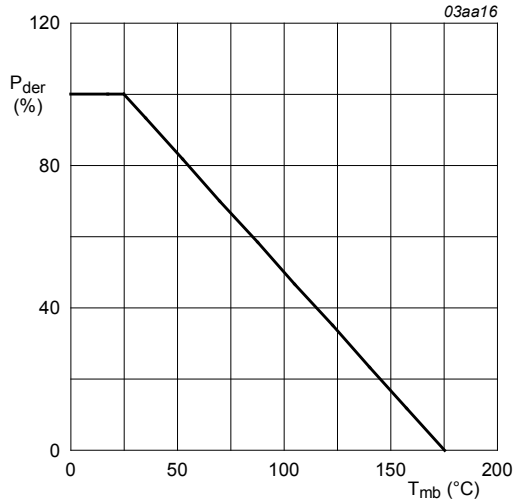
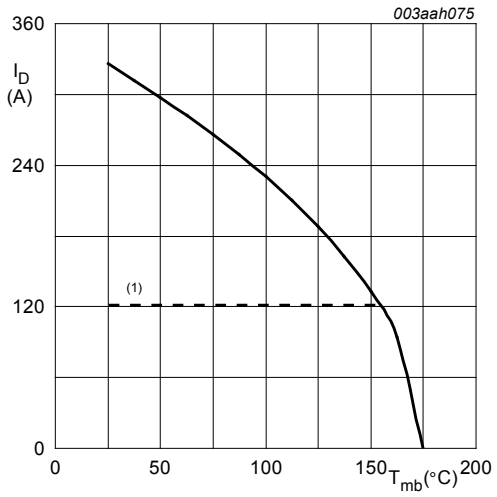


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$



(1) Capped at 120A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10V$$

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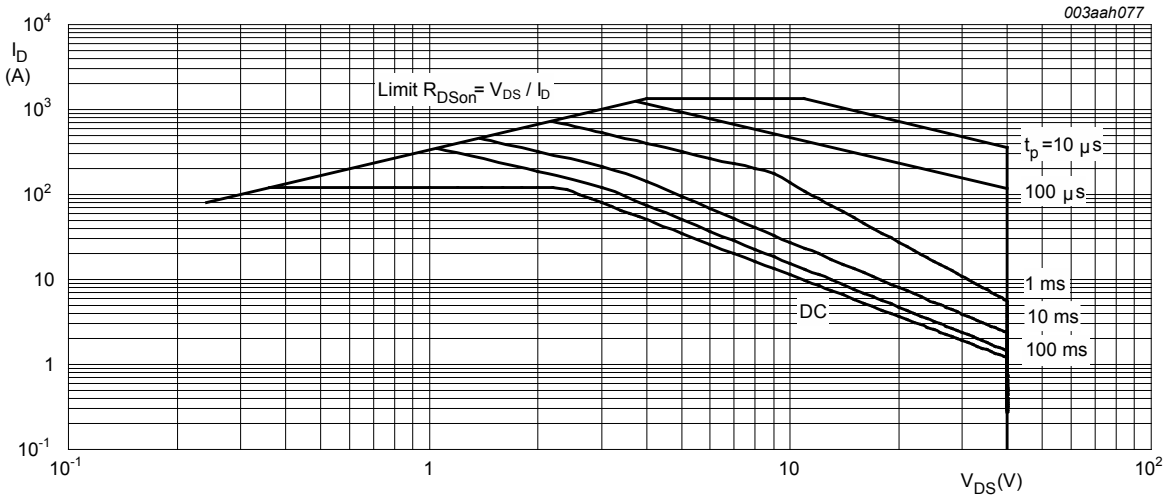


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25°C$; I_{DM} *is a single pulse*

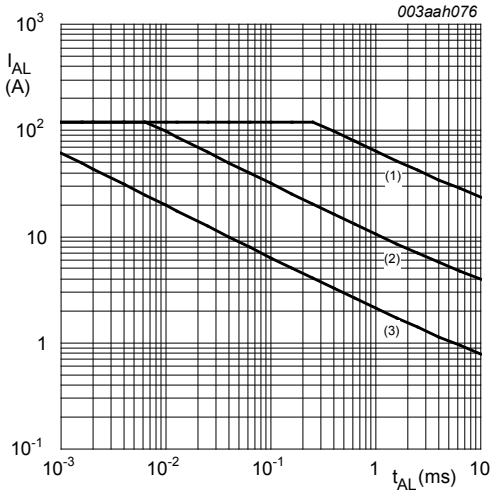


Fig. 4. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j(init)} = 25°C$; (2) $T_{j(init)} = 150°C$; (3) Repetitive Avalanche

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	-	0.46	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board		-	50	-	K/W

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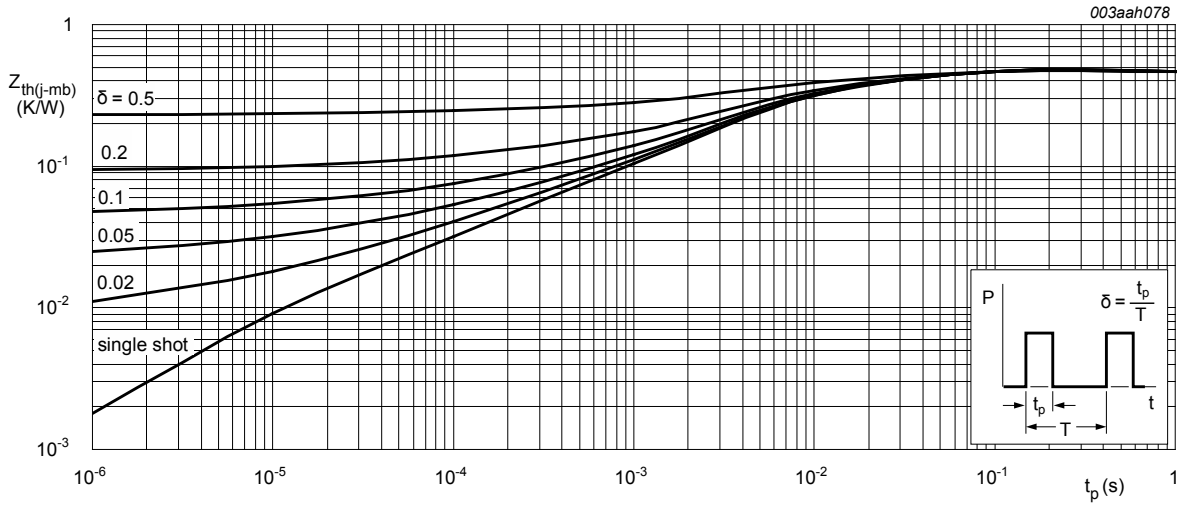


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

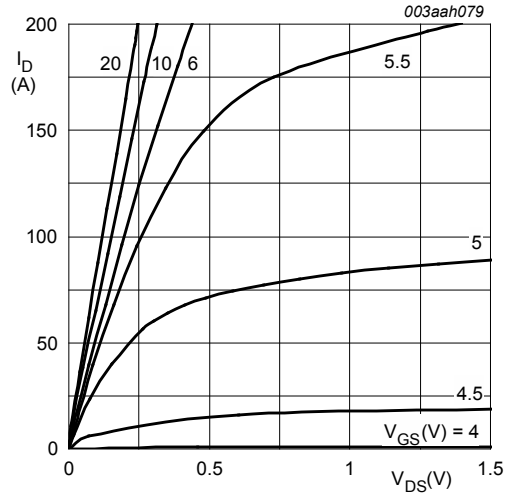
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		40	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS}=V_{GS}; T_j = 25 °C; Fig. 9; Fig. 10		2.4	3	4	V
		I_D = 1 mA; V_{DS}=V_{GS}; T_j = -55 °C; Fig. 10		-	-	4.5	V
		I_D = 1 mA; V_{DS}=V_{GS}; T_j = 175 °C; Fig. 10		1	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C		-	0.27	3	µA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		-	1.32	1.6	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 12; Fig. 11		-	-	3	mΩ
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; Fig. 13; Fig. 14		-	118	-	nC
Q_{GS}	gate-source charge			-	29.3	-	nC
Q_{GD}	gate-drain charge			-	34.7	-	nC

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
C_{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 15		-	7873	10472	pF
C_{oss}	output capacitance			-	1410	1692	pF
C_{rss}	reverse transfer capacitance			-	851	1165	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω		-	35	-	ns
t_r	rise time			-	49	-	ns
$t_{d(off)}$	turn-off delay time			-	87	-	ns
t_f	fall time			-	52	-	ns
L_D	internal drain inductance	from upper edge of drain mounting base to center of die		-	2.5	-	nH
L_S	internal source inductance	from source lead to source bonding pad		-	7.5	-	nH
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 16		-	0.79	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 25 V		-	46	-	ns
Q_r	recovered charge			-	62	-	nC



T_j = 25 °C; t_p = 300 µs

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

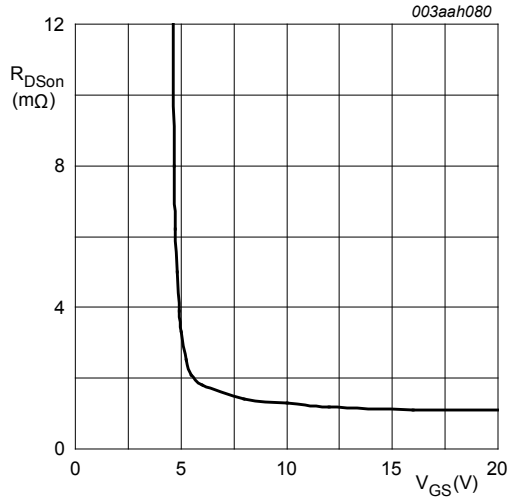


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25°C;\ I_D = 25A$

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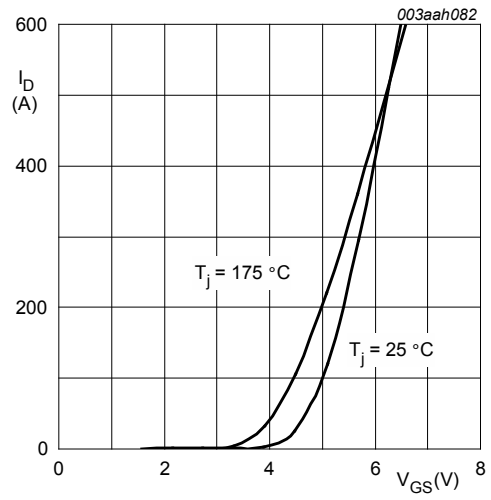


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$

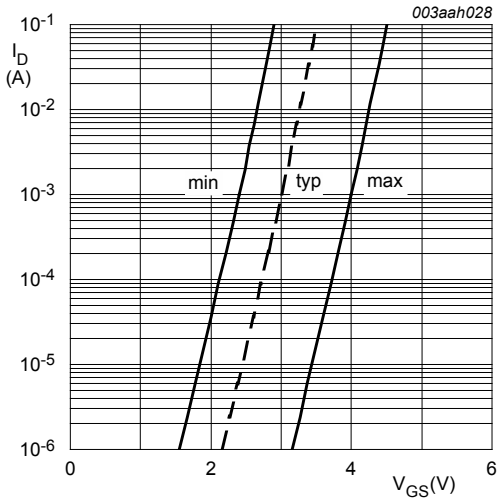


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25°C;\ V_{DS} = 5V$

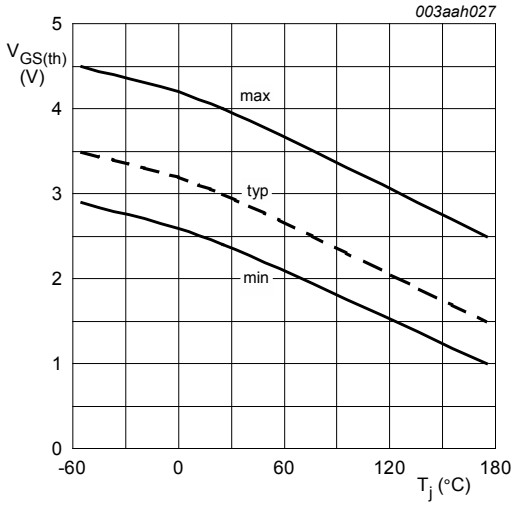
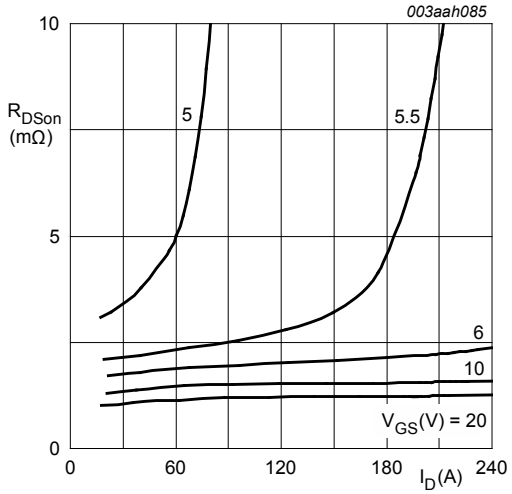


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1$ mA; $V_{DS} = V_{GS}$



T_j = 25 °C; t_p = 300 µs

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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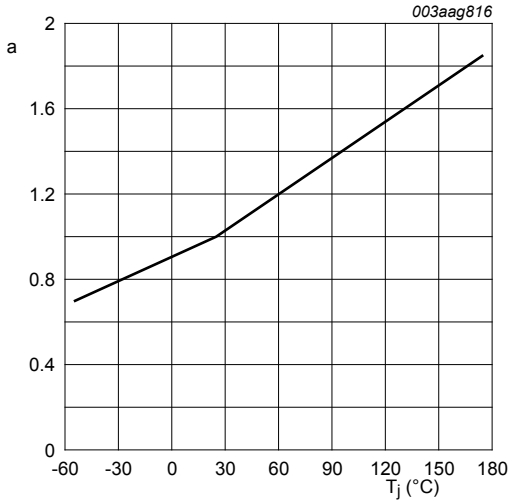


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25\,°C)}}$$

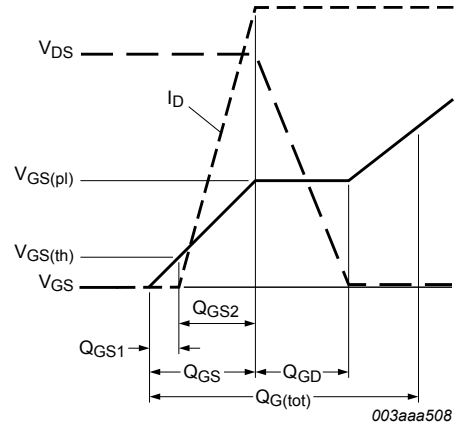


Fig. 13. Gate charge waveform definitions

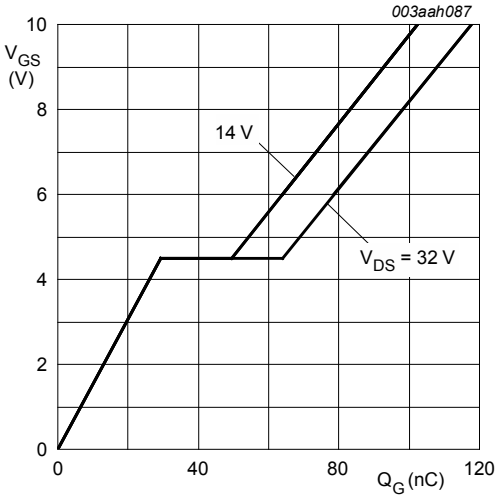


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25°C;\ I_D = 25A$$

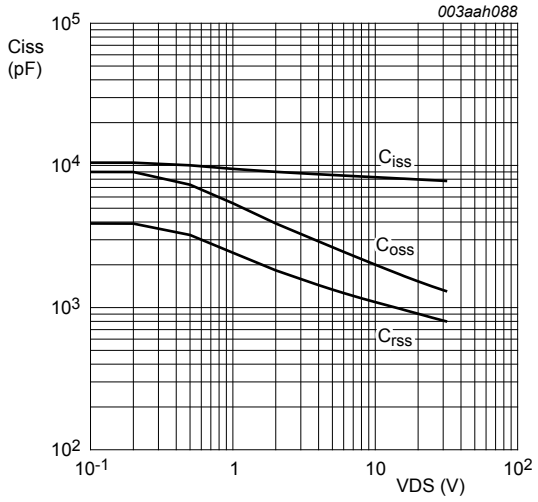


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V;\ f = 1MHz$$

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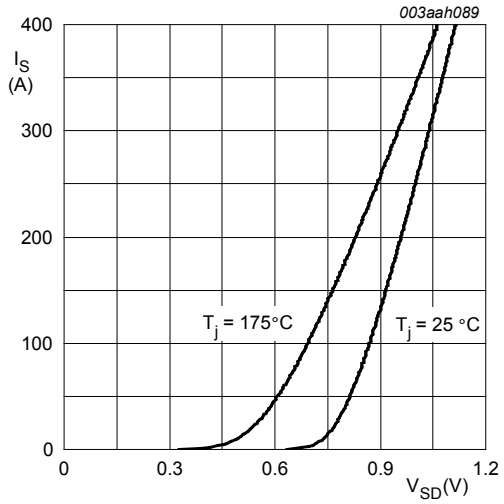


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

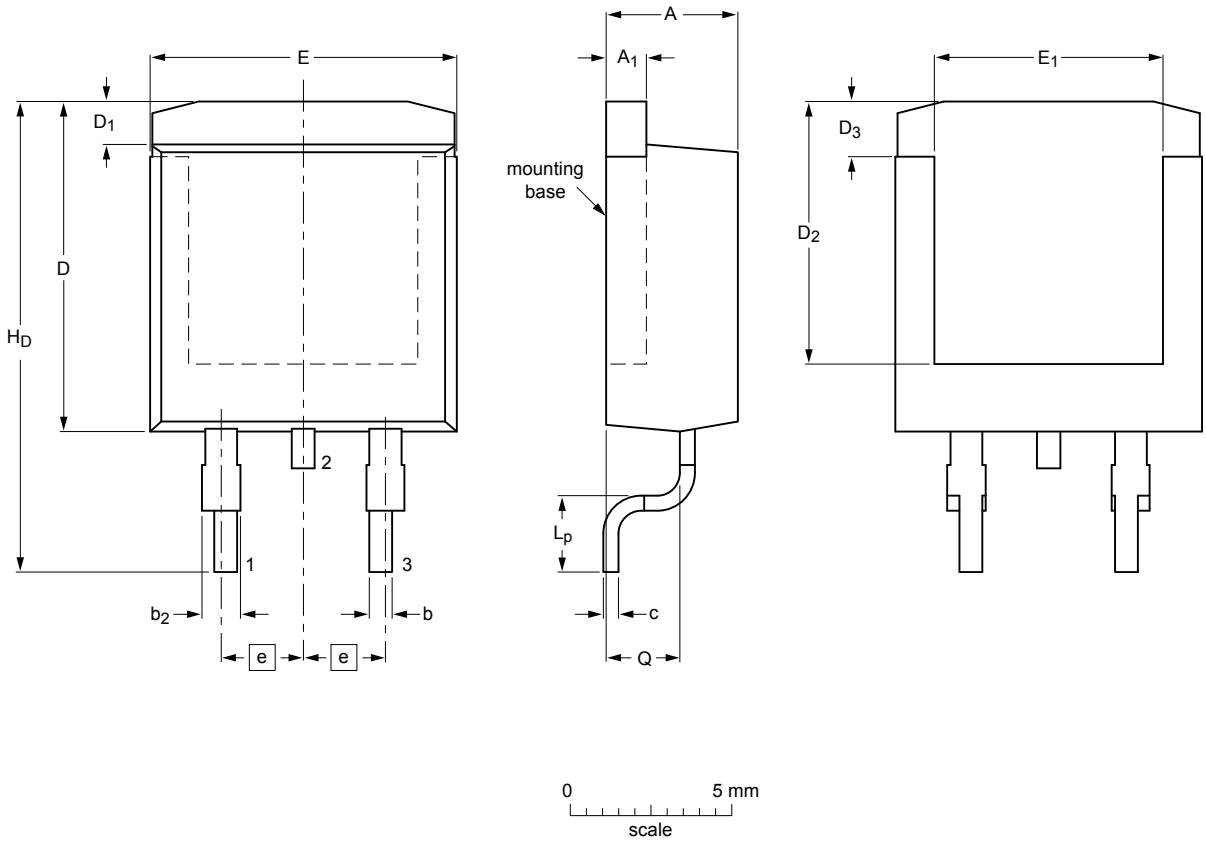
$V_{GS} = 0V$

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11. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) **SOT404A**



Dimensions (mm are the original dimensions)

Unit		A	A_1	b	b_2	c	D_{max}	D_1	D_2	D_3	E	E_1	e	H_D	L_p	Q
mm	max	4.5	1.40	0.85	1.45	0.64	11	1.6	8.6	1.85	10.3	8.1		15.8	2.9	2.6
	nom												2.54			
	min	4.1	1.27	0.60	1.05	0.46		1.2	8.0	1.40	9.7	7.6		14.8	2.1	2.2

sot404a_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT404A						~~13-02-28~~ 13-03-12

Fig. 17. Package outline D2PAK (SOT404A)

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12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
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